**Product data sheet** 

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in an MLPAK33 (SOT8002) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Logic-level compatible
- Trench MOSFET technology
- Ultra low Q<sub>G</sub> and Q<sub>GD</sub> for high system efficiency, especially at higher switching frequencies
- · Superfast switching with soft-recovery
- · Low spiking and ringing for low EMI designs
- MLPAK33 package (3.3 x 3.3 mm footprint)

### 3. Applications

- DC to DC conversion
- · Battery management
- · Low-side load switch
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	30	V
V <sub>GS</sub>	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	$V_{GS} = 10 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	[1]	-	-	12	Α
Static characte	ristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 7.9 A; $T_j$ = 25 °C		-	14.8	17.4	mΩ
		$V_{GS}$ = 4.5 V; $I_D$ = 6.8 A; $T_j$ = 25 °C		-	18.5	23.1	mΩ
Dynamic chara	cteristics						
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = 15 V; $I_{D}$ = 6.8 A; $V_{GS}$ = 4.5 V; $T_{j}$ = 25 °C		-	2.5	3.8	nC

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	1 2 3 4	
2	S	source		
3	S	source		D —
4	G	gate	K	
5	D	drain		G (F)
6	D	drain	l Gaaay	mbb076 S
7	D	drain	8 7 6 5	
8	D	drain	MLPAK33 (SOT8002-1)	

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package						
	Name	Description	Version				
PXN017-30QL		plastic thermal enhanced surface mounted package; mini leads; 8 terminals; pitch 0.65 mm; $3.3 \times 3.3 \times 0.8$ mm body	SOT8002-1				

## 7. Marking

### **Table 4. Marking codes**

Type number	Marking code
PXN017-30QL	9AB

## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	30	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	12	Α
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	7.9	Α
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	5	Α
		V <sub>GS</sub> = 10 V; T <sub>sp</sub> = 25 °C		-	20	Α
I <sub>DM</sub>	peak drain current	T <sub>amb</sub> = 25 °C; single pulse; t <sub>p</sub> ≤ 10 μs		-	163	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	3.8	W
		T <sub>amb</sub> = 25 °C	[1]	-	1.7	W
		T <sub>sp</sub> = 25 °C		-	10.9	W
T <sub>j</sub>	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drain	diode				•	
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	1.6	Α
Avalanche ru	ggedness			'		,
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$T_{j(init)}$ = 25 °C; $I_D$ = 1 A; DUT in avalanche (unclamped)		-	15	mJ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

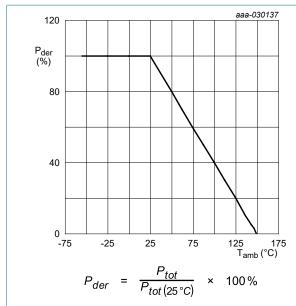


Fig. 1. Normalized total power dissipation as a function of ambient temperature

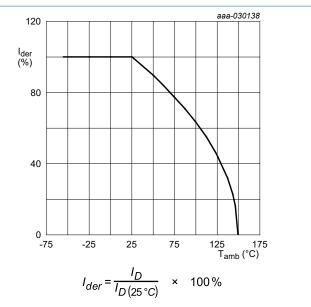


Fig. 2. Normalized continuous drain current as a function of ambient temperature

### 30 V, N-channel Trench MOSFET

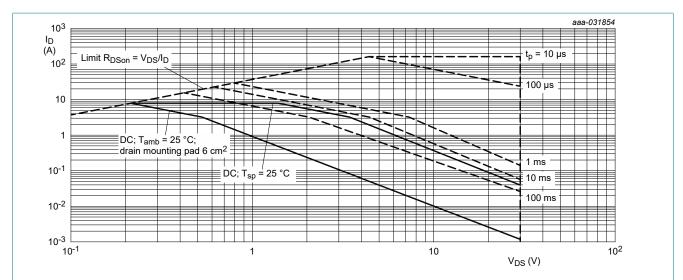


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
ui(j-a)	thermal resistance from	<u> </u>	[1]	-	160	200	K/W
	junction to ambient		[2]	-	60	75	K/W
		in free air; t ≤ 5 s	[2]	-	28	33	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	8.3	11.5	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

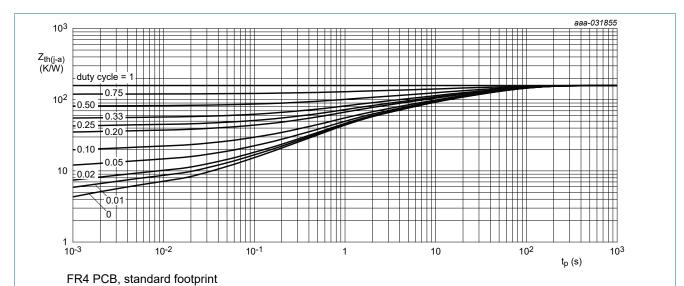


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

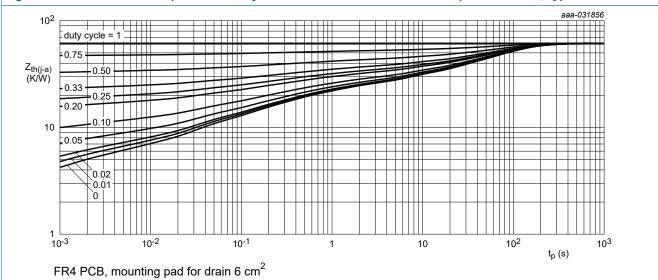


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 °C$	1.2	1.7	2.2	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = 10 \text{ V}; I_D = 7.9 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	14.8	17.4	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 7.9 A; T <sub>j</sub> = 150 °C	-	22.9	27	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 6.8 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	18.5	23.1	mΩ
g <sub>fs</sub>	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 7.9 \text{ A}; T_j = 25 \text{ °C}$	-	15	-	S
$R_{G}$	gate resistance	f = 1 MHz	-	3	-	Ω
Dynamic ch	naracteristics	•		-	<u> </u>	
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = 15 V; $I_{D}$ = 7.9 A; $V_{GS}$ = 10 V; $T_{j}$ = 25 °C	-	5.1	7.7	nC
		V <sub>DS</sub> = 15 V; I <sub>D</sub> = 6.8 A; V <sub>GS</sub> = 4.5 V;	-	2.5	3.8	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	0.9	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge	_	-	0.5	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate- source charge		-	0.4	-	nC
$Q_{GD}$	gate-drain charge		-	0.7	-	nC
$V_{GSpl}$	gate-source plateau voltage	$V_{DS}$ = 15 V; $I_D$ = 6.8 A; $T_j$ = 25 °C	-	2.5	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 15 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	350	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	186	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	21	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 15 V; I <sub>D</sub> = 6.8 A; V <sub>GS</sub> = 4.5 V;	-	5	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C$	-	8	-	ns
t <sub>d(off)</sub>	turn-off delay time	1	-	6	-	ns
t <sub>f</sub>	fall time	1	-	3	-	ns
Source-drai	in diode	1	1	<u> </u>		1
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 1.6 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.7	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 1.6 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	15	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = 4.5 \text{ V}; V_{DS} = 15 \text{ V}; T_j = 25 \text{ °C}$	-	6	-	nC
t <sub>a</sub>	reverse recovery rise time		-	8	-	ns
t <sub>b</sub>	reverse recovery fall time		-	7	-	ns

#### 30 V, N-channel Trench MOSFET

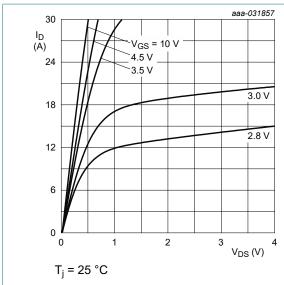


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

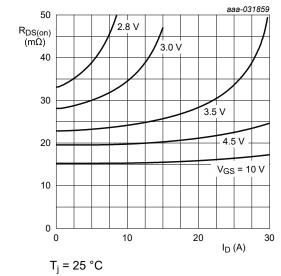


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

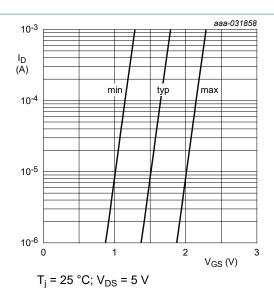


Fig. 7. Subthreshold drain current as a function of gate-source voltage

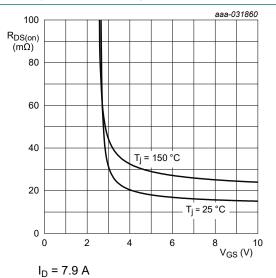


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

#### 30 V, N-channel Trench MOSFET

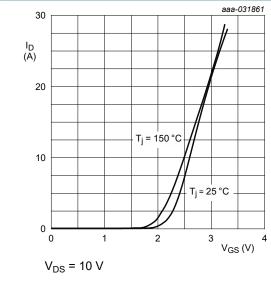


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

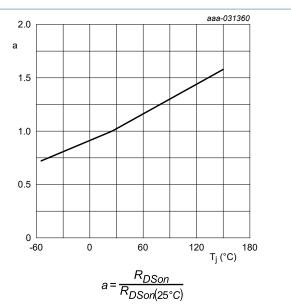


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

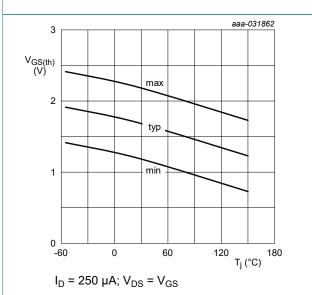
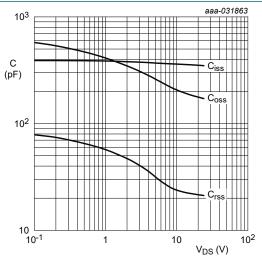


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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#### 30 V, N-channel Trench MOSFET

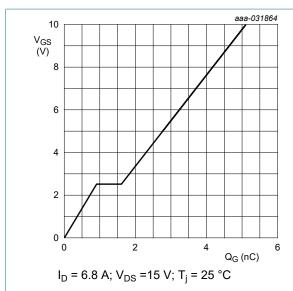


Fig. 14. Gate-source voltage as a function of gate charge; typical values

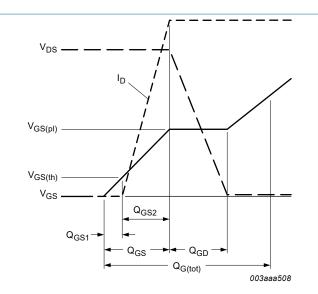


Fig. 15. Gate charge waveform definitions

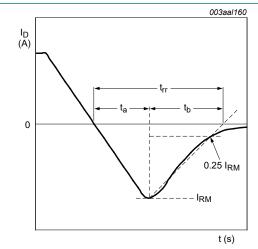


Fig. 16. Reverse recovery timing definition

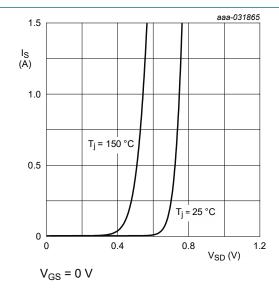
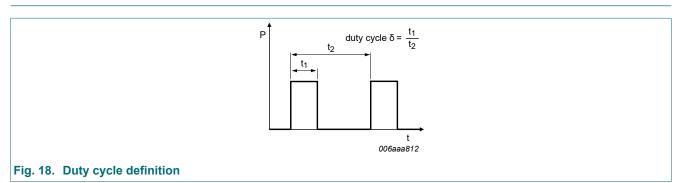


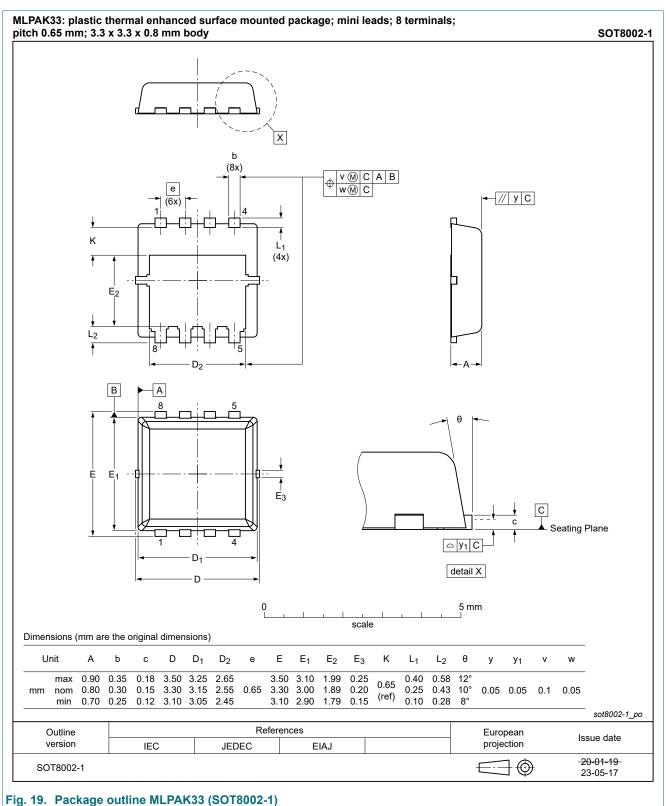
Fig. 17. Source current as a function of source-drain voltage; typical values

### 11. Test information

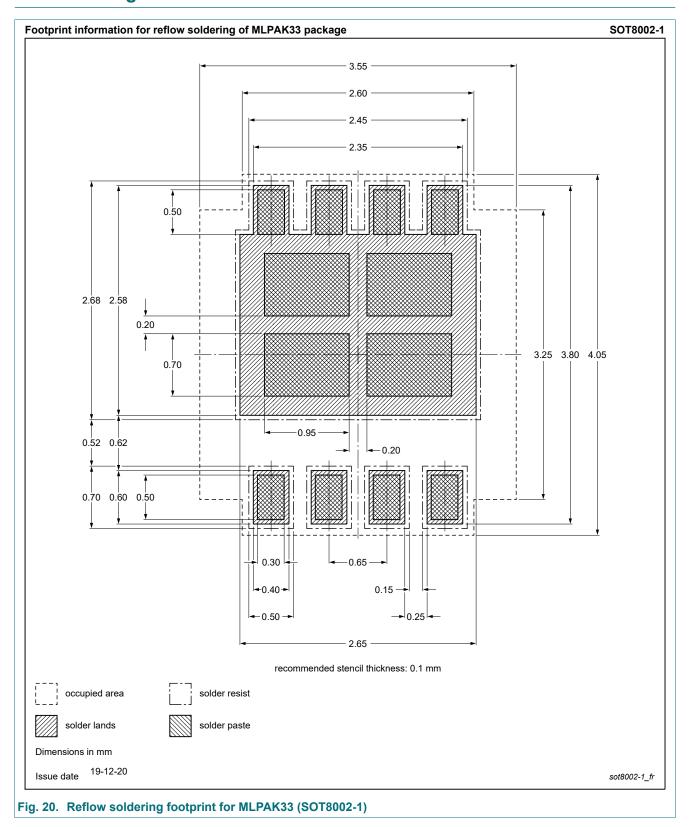


PXN017-30QL

## 12. Package outline



## 13. Soldering



30 V, N-channel Trench MOSFET

# 14. Revision history

#### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PXN017-30QL v.2	20230731	Product data sheet	-	PXN017-30QL v.1			
Modifications:	Chapter "Package outline": drawing update						
PXN017-30QL v.1	20201102	Product data sheet	-	-			

### 15. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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### 30 V, N-channel Trench MOSFET

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	Features and benefits

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